

2SD1739

Silicon PNP Triple-Diffused Planar Type

Horizontal Deflection Output

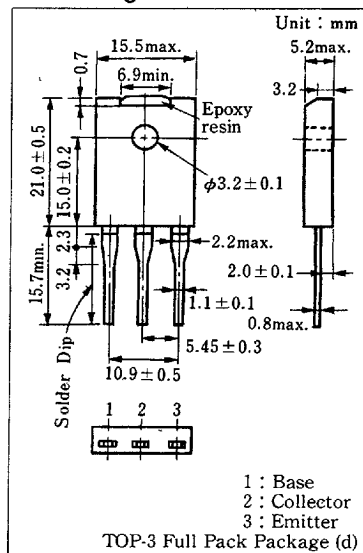
■ Features

- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings (T_c=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V _{CB0}	1500	V
Collector-emitter voltage	V _{CES}	1500	V
	V _{CEO}	700	V
Emitter-base voltage	V _{EBO}	7	V
Peak collector current	I _{CP}	18	A
Collector current	I _C	6	A
Base current	I _B	2.5	A
Collector power dissipation	P _C	100	W
		3	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 ~ +150	°C

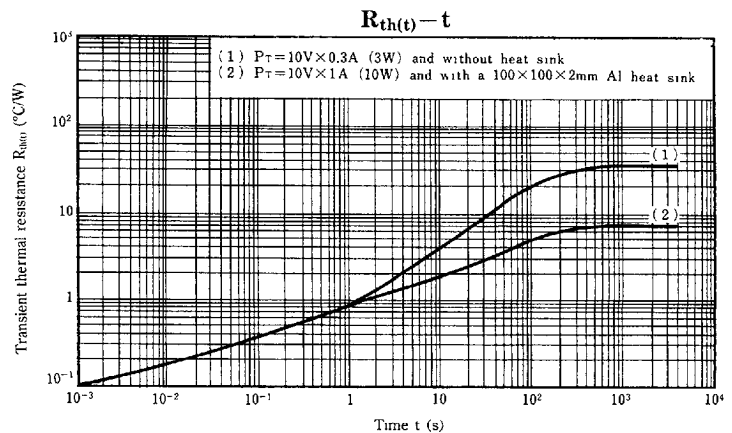
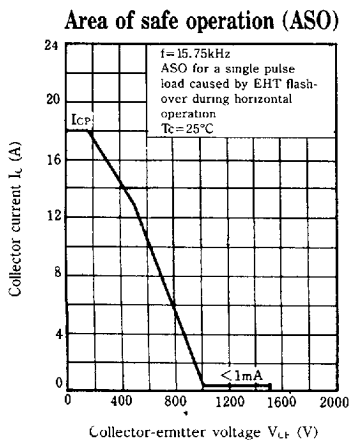
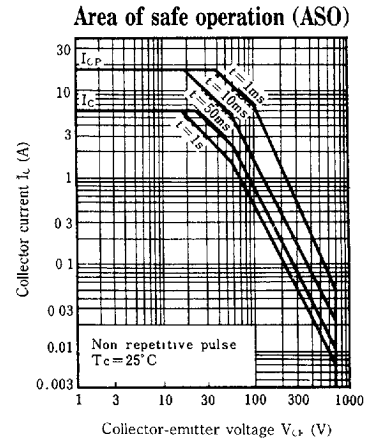
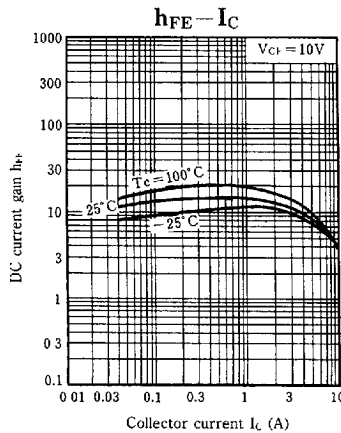
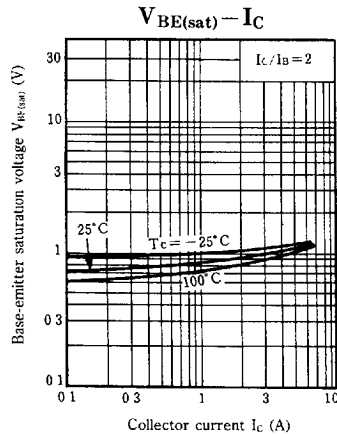
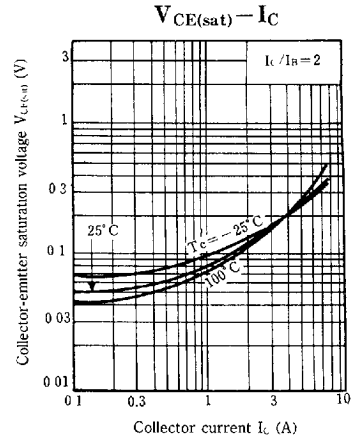
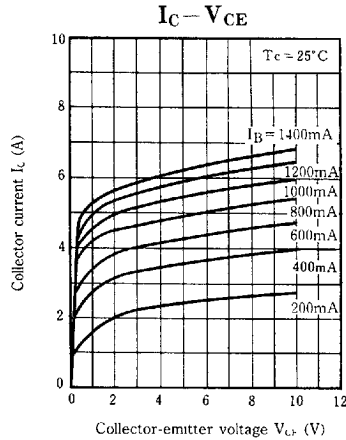
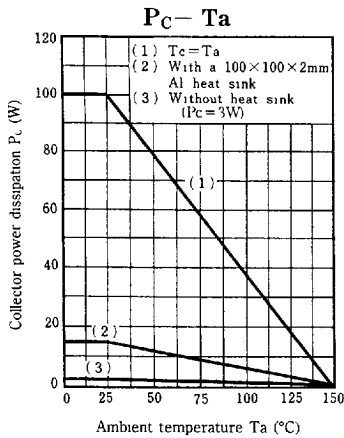
■ Package Dimensions



■ Electrical Characteristics (T_c=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CBO}	V _{CB} =750 V, I _E =0			10	μA
		V _{CB} =1500 V, I _E =0			1	mA
Emitter-base voltage	V _{EBO}	I _E =1mA, I _C =0	7			V
DC current gain	h _{FE}	V _{CE} =5V, I _C =1 A	6		30	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =5 A, I _B =1.2 A			8	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =5 A, I _B =1.2 A			1.5	V
Transition frequency	f _T	V _{CE} =10V, I _C =1A, f=0.5MHz		2		MHz
Storage time (L load)	t _{stg}	I _C =5 A, I _{B1} =1.2 A			10	μs
Fall time (L load)	t _f	I _{B2} =-1.2 A, L _B =5 μH			0.8	μs
Storage time (R load)	t _{stg}	I _C =5 A, I _{B1} =1 A		1.5		μs
Fall time (R load)	t _f	I _{B2} =-2 A, V _{CC} =200 V		0.2		μs

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Panasonic